

WHAT IS CLAIMED IS:

1. A semiconductor laser device, comprising: an oxide having a specified reflectance formed as a protective coating on light emitting end surfaces of a semiconductor laser chip; and

an Si film having a film thickness of 40 Å or less formed between at least one light emitting end surface and the oxide.

2. The semiconductor laser device as claimed in Claim 1, wherein

the Si film has a film thickness of 5 Å or more and 30 Å or less.

3. The semiconductor laser device as claimed in Claim 1, wherein

the oxide constituting the protective coating is an Al_2O_3 film.

4. The semiconductor laser device as claimed in Claim 1, wherein

the semiconductor laser chip has an active layer containing Al.

5. The semiconductor laser device as claimed in Claim 1, wherein

the Si film has purity of 99.99% or more.

6. A method for manufacturing the semiconductor laser device as claimed in Claim 1, comprising

a step of forming the Si film and the oxide on the light emitting end surface, the step being executed in succession within same equipment without exposing the surface to the air.

- 5 7. A method for manufacturing the semiconductor laser device as claimed in Claim 1, comprising

a step of forming the Si film and the oxide through vacuum deposition.